

# **isc** Silicon NPN Power Transistor

# 2SC4706

### DESCRIPTION

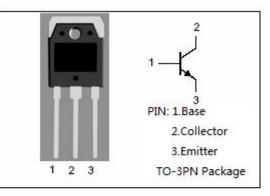
- High Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 600V(Min)
- High Switching Speed
- High Reliability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

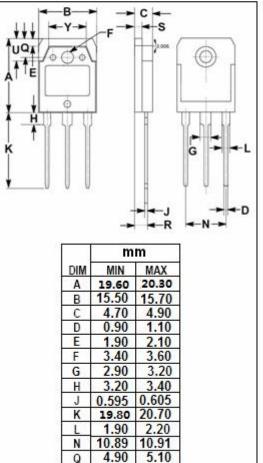
### **APPLICATIONS**

• Designed for switching regulator and general purpose applications.

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ABSOLUTE MAXIMUM RATINGS(Ta=25°C)							
PARAMETER	VALUE	UNIT					
Collector-Base Voltage	900	V					
Collector-Emitter Voltage	600	600 V					
Emitter-Base voltage	7	V					
Collector Current-Continuous	14	A					
Collector Current-Peak	28	A					
Base Current-Continuous	7	A					
Collector Power Dissipation @ Tc=25℃	130	W					
Junction Temperature	150	°C					
Storage Temperature Range	-55~150	°C					
	PARAMETER   Collector-Base Voltage   Collector-Emitter Voltage   Emitter-Base voltage   Collector Current-Continuous   Collector Current-Peak   Base Current-Continuous   Collector Power Dissipation   @ Tc=25°C   Junction Temperature	PARAMETERVALUECollector-Base Voltage900Collector-Emitter Voltage600Emitter-Base voltage7Collector Current-Continuous14Collector Current-Peak28Base Current-Continuous7Collector Power Dissipation @ Tc=25°C130Junction Temperature150					





## isc website: <u>www.iscsemi.com</u>

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### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	600			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 1.4A			0.5	V
$V_{\text{BE}(\text{sat})}$	Base-Emitter Saturation Voltage	I <sub>C</sub> = 7A; I <sub>B</sub> = 1.4A			1.2	V
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 800V ; I <sub>E</sub> = 0			0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			0.1	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 7A ; V <sub>CE</sub> = 4V	10		25	
Сов	Output Capacitance	I <sub>E</sub> = 0 ; V <sub>CB</sub> = 10V; f <sub>test</sub> =1.0MHz		160		pF
fT	Current-Gain—Bandwidth Product	I <sub>E</sub> = -1.5A ; V <sub>CE</sub> = 12V		6		MHz

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